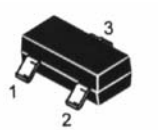
Transys Electronics LIMITED

SOT-323 Plastic-Encapsulated Transistors

MMSTA92 TRANSISTOR (PNP)

SOT-323



1. BASE
2. EMITTER
3. COLLECTOR

Unit: mm

FEATURES

Power dissipation

$P_{CM:}$ 0.2 W (Tamb=25℃)

Collector current

$I_{CM:}$ -0.3 A

Collector-base voltage

$V_{(BR)CBO}$: -310 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -100μA, I_E=0	-310			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= -1 mA, I_B=0	-305			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -200V, I_E=0			-0.25	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -10V, IC=- 1 mA	60			
	$h_{FE(2)}$	V_{CE}= -10V, I_C = -10 mA	100		200	
	$h_{FE(3)}$	V_{CE}= -10 V, I_C= -80 mA	60			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C= -20 mA, IB= -2 mA			-0.2	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C= -20 mA, IB= -2 mA			-0.9	V
Transition frequency	f_T	V_{CE}= -20 V, IC= -10 mA f = 30MHz	50			MHz

DEVICE MARKING

MMSTA92=K3R